UNISONIC TECHNOLOGIES CO., LTD

4128D

Preliminary

NPN EPITAXIAL SILICON TRANSISTOR

MIDDLING VOLTAGE **FAST-SWITCHING NPN** POWER TRANSISTOR

DESCRIPTION

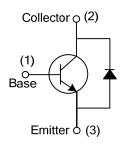
The UTC 4128D is a middling voltage NPN power transistor. it uses UTC's advanced technology to provide customers with high switching speed and high reliability, etc.

The UTC 4128D is suitable for commonly power amplifier circuit, electronic ballasts and energy-saving light etc.

FEATURES

- * High switching speed
- * High reliability

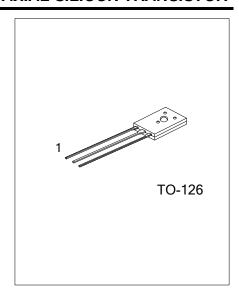
SYMBOL



ORDERING INFORMATION

	Ordering	Dookooo	Pin Assignment			Dealing		
	Lead Free	Halogen Free	Package	1	2	3	Packing	
	4128DL-T60-K 4128DG-T60-K		TO-126	В	С	E	Bulk	
Note: Pin Assignment: B: Base C: Collector E: Em			ter	•	•		•	

Note: Pin Assignment: B: Base C: Collector 4128DL-T60-T - (1)Packing Type (1) B: Bulk (2)Package Type (2) T60: TO-126 - (3)Lead Free (3) L: Lead Free, G: Halogen Free



1 of 3

■ ABSOLUTE MAXIMUM RATINGS (T_C=25°C)

PARAMETER		SYMBOL	RATINGS	UNIT
Collector-Emitter Voltage (V _{BE} =0)		V _{CES}	350	V
Collector-Emitter Voltage (I _B =0)		V_{CEO}	200	V
Emitter-Base Voltage		V_{EBO}	7	V
Calla atau Cumant	DC	Ic	5	Α
Collector Current	Pulse (Note 2)	I _{CP}	10	Α
Deep Current	DC	I _B	2	Α
Base Current	Pulse (Note 2)	I _{BP}	4	Α
Total Dissipation		Pc	40	W
Junction Temperature		T_J	150	°C
Storage Temperature Range		T _{STG}	-55~+150	°C

Notes: 1. Absolute maximum ratings are stress ratings only and functional device operation is not implied. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

■ THERMAL CHARACTERISTICS

PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Case	θıc	3.125	°C/W

■ ELECTRICAL CHARACTERISTICS

PARAMETER	SYMBOL	TEST CONDITIONS		TYP	MAX	UNIT
Collector-Base Breakdown Voltage	BV _{CBO}	I _C =1mA, I _B =0				V
Collector-Emitter Breakdown Voltage	BV_CEO	I _C =10mA, I _B =0	200			V
Emitter-Base Breakdown Voltage	BV_{EBO}	I _E =1mA, I _C =0				V
Collector Cut-Off Current	I _{CBO}	V _{CB} =350V, I _E =0			100	μΑ
Collector-Emitter Cut-Off Current	I _{CEO}	V _{CE} =200V, I _B =0			50	μΑ
Emitter Cut-Off Current	I _{EBO}	V_{EB} =7V, I_C =0			10	μΑ
Callegtor Emitter Seturation Voltage	$V_{CE(SAT)1}$	I _C =1A, I _B =0.2A			0.8	V
Collector-Emitter Saturation Voltage	$V_{CE(SAT)2}$	I _C =3A, I _B =0.6A			1.5	V
Base-Emitter Saturation Voltage	$V_{BE(SAT)}$	I _C =3A, I _B =0.6A			1.6	V
DC Current Cain	h _{FE1}	I _C =0.8A,V _{CE} =5V	8		50	
DC Current Gain	h _{FE2}	$I_C=3A,V_{CE}=5V$	8			
Transition Frequency	f_T	I _C =0.5A, V _{CE} =10V	4			MHz
Storage Time	ts	\\ -24\\ -0.5A - -0.1A			4	μs
Fall Time	t_{F}	V _{CC} =24V, I _C =0.5A, I _{B1} =-I _{B2} =0.1A			0.7	μs

^{2.} Pulse Test: Pulse Width=5.0ms, Duty Cycle<10%.

UTC assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all UTC products described or contained herein. UTC products are not designed for use in life support appliances, devices or systems where malfunction of these products can be reasonably expected to result in personal injury. Reproduction in whole or in part is prohibited without the prior written consent of the copyright owner. The information presented in this document does not form part of any quotation or contract, is believed to be accurate and reliable and may be changed without notice.

